

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, PLASTIC, NPN,
SILICON, SWITCHING, LOW NOISE TYPE 2N2484UE1
JAN, JANTX, JANJ

This specification is approved for use by all Departments
and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for plastic NPN, silicon, switching, low noise transistors. Three levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1, SOT-23 (similar to TO-236).

1.3 Maximum ratings.

Types	P _T	V _{CB0}	V _{EBO}	V _{CEO}	I _C	T _J and T _{STG}	R _{θJA}
	T _A = +25°C						
2N2484UE1	$\frac{\text{mW}}{500}$	$\frac{\text{V dc}}{60}$	$\frac{\text{V dc}}{6}$	$\frac{\text{V dc}}{60}$	$\frac{\text{mA dc}}{50}$	$^{\circ}\text{C}$ -55 to +150	$\frac{^{\circ}\text{C/W}}{320 (1)}$ 450 (2)

- (1) If the printed wiring board is made of alumina substrate; alumina = 0.4 x 0.3 x 0.024 in., 99.5 percent alumina: Derate linearly 2.4 mW/°C for T_A > +25°C.
- (2) If the printed wiring board is made of FR5 substrate; FR5 = 1.0 x .75 x .062 inches (25.4 x 19.05 x 1.57 mm). Derate linearly 1.8 mW/°C for T_A > +25°C.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center, Columbus, ATTN: DSCC/VAC, Post Office Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

1.4 Primary electrical characteristics at $T_A = +25^\circ\text{C}$.

	h_{fe}	C_{obo}	$ h_{fe} ^2$	$V_{CE(sat)}$ (1)
Limits	$V_{CE} = 5\text{ V dc}$ $I_C = 1\text{ mA dc}$ $f = 1\text{ kHz}$	$I_E = 0$ $V_{CB} = 5\text{ V dc}$ $100\text{ kHz} \leq f \leq 1\text{ MHz}$	$I_C = 500\text{ }\mu\text{A dc}$ $V_{CE} = 5\text{ V dc}$ $f = 30\text{ MHz}$	$I_C = 1.0\text{ mA dc}$ $I_B = 0.1\text{ mA dc}$
		μF		V dc
Min	250		2.0	
Max	900	5.0	7.0	0.3

(1) Pulsed (see 4.5.1).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement there to, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

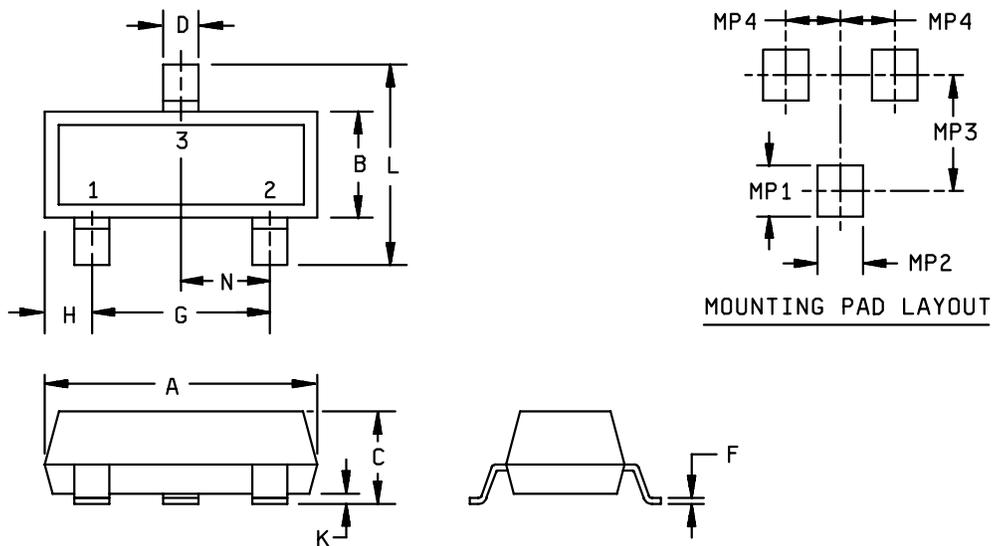
MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Document Automation and Production Services (DAPS), Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Terminal numbers are shown for reference.
1 = Base, 2 = Emitter, 3 = Collector

Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
A	.110	.123	2.8	3.1
B	.051	.057	1.32	1.43
C	.037	.046	0.95	1.15
D	.015	.017	0.39	0.41
F	.005	.007	0.125	0.175
G	.074	.076	1.88	1.92
H	.018	.024	0.46	0.59
K	0	.004	0	0.1
L	.094	.103	2.4	2.6
N	.037	.038	0.94	0.96
MP1	.035	.036	0.89	0.91
MP2	.031	.032	0.79	0.81
MP3	.078	.080	1.99	2.01
MP4	.037	.038	0.94	0.96

FIGURE 1. Physical dimensions (SOT-23, similar to TO-236).

2.3 Non-Government publications. The following documents form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DoDISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DoDISS are the issues of the documents cited in the solicitation (see 6.2).

JEDEC Standard 20	-	Moisture Reflow Sensitivity Classification for Surface Mount Devices.
JESD22-A101	-	Steady State Temperature Humidity Bias Life Test.
JESD22-A102	-	Autoclave.
JESD22-A103	-	High temperature storage life.
JESD22-A112	-	ESD Testing.
JESD22-A113	-	Preconditioning.

(Applications for copies should be addressed to the Electronics Industries Alliance, 2500 Wilson Boulevard, Arlington, VA 22201-3834.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents may also be available in or through libraries or other informational services.)

2.4 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The requirements for acquiring the product described herein shall consist of this document and MIL-PRF-19500.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500 and as follows.

FIT - Failure in time.

UE1 - Unleaded encapsulated plastic over epoxy wire bonded frame (non-hermetic).

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500, and figure 1 herein.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.6 Electrical test requirements. The electrical test requirements shall be group A as specified herein.

3.7 Marking. Marking shall be in accordance with MIL-PRF-19500, except as specified herein. The part marking shall consist of an abbreviated date code (Y, M), JAN brand (J), manufacturer code (m), and part number code (E) due to space limitations (see figure 2).

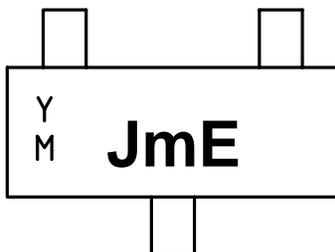


FIGURE 2. Part marking orientation.

3.7.1 Date code. The date code shall be as follows:

- a. 1st character: Designator of the manufacturing year, where Y will be "M" through "Z" to indicate the year. The sequence starts back at "A" after the year 2011. This sequence will repeat every 24 years. Letters "I" and "O" will not be used.

2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
M	N	P	R	S	T	U	V	W	X	Y	Z	A

- b. 2nd character: Designator of the manufacturing month, where M will be "1" through "D" to indicate the month.

JAN	FEB	MAR	APR	MAY	JUN	JUL	AUG	SEP	OCT	NOV	DEC
1	2	3	4	5	6	7	8	9	O	N	D

3.7.2 JAN brand. The "J" denotes the JAN brand. Refer to the certificate of conformance or unit packaging for quality assurance level.

3.7.3 Manufacturers code. The "m" denotes the manufacturer. The letter "A" is assigned to manufacturer CAGE code 14936. Contact the preparing activity for new letter assignments.

3.7.4 Part code. The 'E' is the part number code on a TO-236AB (SOT-23) for a 2N2484UE1.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 JANJ qualification. For JANJ qualification, 4.4.2.1 herein shall be performed as required by the qualifying activity.

4.2.2 JANJ devices. For JANJ level, 3.3.1 through 3.3.1.3 of MIL-PRF-19500 shall apply, except as modified herein. Supplier imposed requirements as well as alternate screens, procedures, and/or controls shall be documented in the QM plan and must be submitted to the qualifying activity for approval. When alternate screens, procedures, and/or controls are used, in lieu of the JANJ screens herein equivalency shall be proven and documented in the QM plan. Radiation characterization may be submitted in the QM plan at the option of the manufacturer, however, 3.3.1.1 of MIL-PRF-19500 is not required. Die lot control and rework for JANJ shall be in accordance with the JANS requirements of 3.13 and D3.13.2.1 of MIL-PRF-19500. Lot formation and conformance inspection requirements for JANJ shall be those used for JANTXV devices as a minimum.

4.3 Screening (JANJ, JANTX). For appendix D qualified suppliers, screening shall be in accordance with table IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable. For appendix C qualified suppliers (QML), and for JANJ, refer to QM plan for screening requirements. The level of screening for screens 3a, 10, and 12 will be determined based on the reliability FIT level (see 4.3.1).

Screen (see table IV of MIL-PRF-19500)	Measurement		
	JANS Level (for reference only)	JANJ Level	JANTX Level
1a	Not applicable	Not applicable	Not required
1b	Required	Required	Not required
2	Not required	Not required	Not required
3a	Required	Required	Required
3b	Not applicable	Not applicable	Not applicable
(1) 3c	Thermal impedance (see 4.3.3)	Thermal impedance (see 4.3.3)	Thermal impedance (see 4.3.3)
4	Not applicable	Not applicable	Not applicable
5	Not applicable	Not applicable	Not applicable
6	Not applicable	Not applicable	Not applicable
7a	Not applicable	Not applicable	Not applicable
7b	Not applicable	Not applicable	Not applicable
8	Required	Wafer level traceability	Not required
9	I_{CBO2} , h_{FE4}	I_{CBO2} , h_{FE4}	Not applicable
10	Method 1039 of MIL-STD-750, condition A 48 hrs minimum	Method 1039 of MIL-STD-750, condition A 48 hrs minimum	Method 1039 of MIL-STD-750, condition A 48 hrs minimum
11	I_{CBO2} ; h_{FE4} ; ΔI_{CBO2} = 100 percent of initial value or 2 nA dc, whichever is greater. Δh_{FE4} = ± 15 percent	I_{CBO2} ; h_{FE4} ; ΔI_{CBO2} = 100 percent of initial value or 2 nA dc, whichever is greater. Δh_{FE4} = ± 15 percent	I_{CBO2} , h_{FE4}
12	Required 240 hours minimum See 4.3.2	Required 240 hours minimum See 4.3.2	Required 80 hours minimum See 4.3.2
13a	Subgroups 2 of table I herein; ΔI_{CBO2} = 100 percent of initial value or 2 nA dc, whichever is greater; Δh_{FE4} = ± 15 percent	Subgroups 2 of table I herein; ΔI_{CBO2} = 100 percent of initial value or 2 nA dc, whichever is greater; Δh_{FE4} = ± 15 percent	Subgroup 2 of table I herein; ΔI_{CBO2} = 100 percent of initial value or 5 nA dc, whichever is greater; Δh_{FE4} = ± 15 percent
13b	Group A, subgroup 3	1) 100 percent in-line electricals at 85°C 2) Group A, subgroup 3, high temp, 100 percent 3) Group A, subgroup 3, low temp, n = 116, c = 0	Not required
14a	Not applicable	Not applicable	Not applicable
14b	Not applicable	Not applicable	Not applicable
15	Required	Required	Not required
16	Required	Required	Not required

(1) Thermal impedance shall be performed any time after screen 3.

4.3.1 QML JANTX, JANJ screening requirements. The level of screening will be determined by demonstration of reliability performance. The reliability models and methods will be in accordance with the models below. The table below will be used to determine the level of screening for the individual screens based on the reliability performance. NOTE: Each screen test will be determined individually by the reliability performance demonstrated. As an example there can be a demonstrated performance of temperature cycle to a level below $< 6 \times 10^{-9}$ which would result in a screen of the group B temperature cycle test at a $n = 116$, $c = 0$, but the HTRB may only demonstrate a reliability level of ≤ 10 , > 1 , which would require a screen of group B, $n = 500$, $c = 0$. Confidence level will be 60 percent.

Screen Test	Reliability Model (1) (2) (3)	Constants for Model	Unit of measure	Level	Screen level
Temp cycle 3a	Coffin Manson	M = 4 <T use = 55°C	Failure / cycle	$> 6 \times 10^{-8}$	4.3, screening 100 percent (JANJ, JANTX)
				$\leq 6 \times 10^{-8}$, $> 6 \times 10^{-9}$	Group B, n = 500 c = 0
				$< 6 \times 10^{-9}$	Group B, n = 116 c = 0
HTRB 10	Arrhenious	Ea = .7 T _J use = 55°C	FIT	> 10	4.3, screening 100 percent (JANJ, JANTX)
				$\leq 10, > 1$	Group B, n = 500 c = 0
				< 1	Group B, n = 116 c = 0
OP Life 12	Arrhenious	Ea = .7 T _J use = 55°C	FIT	> 10	4.3, screening 100 percent (JANJ, JANTX)
				$\leq 10, > 1$	Group B, n = 500 c = 0
				< 1	Group B, n = 116 c = 0
13b	Group A, subgroup 3 will be in accordance with 4.3, screening table for JANJ				

- (1) Thermal Effects (Arrhenius):

$$A_f = \exp \left[\frac{E_a}{k} \cdot \left(\frac{1}{T_u} - \frac{1}{T_t} \right) \right]$$

T_u = use environment junction temperature (in °K).
 T_t = test environment junction temperature (in °K).
 A_f = acceleration factor.
 k = Boltzman's Constant (8.6171×10^{-5} eV).
 E_a = activation energy, typical value for a given failure mechanism or derived from empirical data.

- (2) Thermo-mechanical Effects (Coffin-Manson):

$$A_f = \left(\frac{\Delta T_t}{\Delta T_u} \right)^m$$

A_f = acceleration factor.
 ΔT_t = thermal cycle temperature change in the test environment.
 ΔT_u = thermal cycle temperature change in the use environment.
 m = constant, typical value for a given failure mechanism or derived from empirical data.

- (3) Failure Rate Estimating Methodology:

$$\lambda = \frac{\chi^2(\alpha, d.f.)}{2 \cdot A_f \cdot t} \cdot 10^9$$

λ = failure rate (Failures-In-Time).
 χ^2 = chi-square function.
 α = (100 - confidence level) / 100.
 $d.f.$ = (2n + 2) degrees of freedom.
 n = number of failures.
 A_f = acceleration factor.
 t = (sample size x total test time) device-hours .

4.3.2 Power burn-in conditions. Power burn-in conditions are as follows: T_A = room ambient as defined in the general requirements of 4.5 of MIL-STD-750; 2N2484UE1: $V_{CB} = 10 - 30$ V dc, power shall be applied to achieve a T_J of +135°C minimum and a minimum power dissipation of 75 percent of rated P_T as defined in 1.3.

4.3.3 Thermal behavior measurements (delta V_{be}). 100 percent screening in accordance with method 3131 of MIL-STD-750.

- a. I_M measurement current ----- 5 mA.
- b. I_H forward heating current ----- 200 mA minimum.
- c. t_H heating time----- 20 - 30 ms.
- d. t_{md} measurement delay time ----- 5 ms maximum.
- e. V_{CE} collector-emitter voltage during heating ----- 10 V dc.

The delta V_{be} limits are fixed to 100 mV minimum and 200 mV maximum.

4.4 Conformance inspection. For appendix D qualified suppliers, conformance inspection shall be in accordance with MIL-PRF-19500, and as specified herein. For appendix C qualified suppliers (QML), and for JANJ, refer to QM plan for "On-Going Reliability Monitor Requirements".

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified in 4.4.2.1 for JAN, JANTX, and JANJ and as follows. Electrical measurements (end-points) for JAN, JANTX and JANJ shall be as specified below. Delta requirements shall be as specified below and shall be the steps of table III herein. Separate samples may be used for each step, however, preconditioning shall be performed on each sample.

<u>Step</u>	<u>Method</u>	<u>Condition</u>
0		Preconditioning: 1-Dipping of devices in a perfluoropolyter liquid: 10 sec. +150°C 2 times. 2-Rinse of devices in deionized water. 3-Dry of the devices at T _A . 4-Thermal cycle: cond. G, 100cycles.
	1051	
1	2026	Solderability: n = 15, c = 0.
2	1051	Temp. cycle: Condition G, 25 cycles, n = 15, c = 0.
3	JESD22-A102	Autoclave: Condition C, 96 hours, n = 15, c = 0.
4	2031	Solder heat: T = +260°C, 10 sec., n = 20, c = 0.
5		PCB simulation.
6	1039	Steady-state operation life: T _J = +135°C minimum, 240 hrs, 20 V, 13.6 mA, T _A = +45°C, n = 45, c = 0.
7	1039	HTRB: +150°C minimum, 168 hours, 48V, n = 45, c = 0.
	Electrical measurements	Group A, subgroup 2.
	Delta shift	See table III.

4.4.2.1 Group B sample selection. Separate samples may be used for each step. In the event of a group B failure, the manufacturer may pull a new sample at double size from either the failed assembly lot or from another assembly lot from the same wafer lot. If the new "assembly lot" option is exercised, the failed assembly lot shall be scrapped. Samples selected for group B inspection for JAN and JANTX shall be selected randomly from a minimum of three wafers (or from each wafer in the lot). JANJ samples will be from each wafer. When the QML screening option is used, (see 4.3.1) the tests used will replace the tests in group B, but the remainder of group B will be performed.

4.4.3 Group C inspection, JAN, JANTX, and JANJ. Group C inspection (JAN, JANTX, and JANJ) shall be as specified in 4.4.3.1 and shall include tests which are performed periodically. Group C test on each structurally identical device grouping shall be performed on devices from each three months production (once per quarter) of devices (based on inspection lot identification codes) for each assembly location and die attach method. When there is a JANJ lot available the JANJ lot will be selected for the sample. Electrical measurements (end-points) shall be as specified below and in accordance with group A, subgroup 2 herein. Delta requirements shall be as specified below and shall be the steps of table III herein. The sample size for each of these steps is: 45 devices, c = 0. Separate samples may be used for each step, however, preconditioning shall be performed on all samples. For rules on resubmission for failed steps, see MIL-PRF-19500 rules on resubmission of failed subgroups.

4.4.3.1 Group C inspection, (JAN, JANTX, JANJ). Separate samples may be used for each step.

<u>Step</u>	<u>Method</u>	<u>Condition</u>
0		Preconditioning: 1-Dipping of devices in a perfluoropolyter liquid: 10 sec. +150°C, 2 times. 2-Rinse of devices in deionized water. 3-Dry of the devices at T _A . 4-Thermal cycle: condition G, 100cycles.
	1051	
1	JESD22-A103	Low temp storage (substitute low temperature condition): -50°C, 1,000 hours.
2	1051	Temp. cycle: condition G, 1,000 cycles.
3	JESD22-A102	Autoclave: condition C, 96 hours.
4	JESD22-A101	Moisture resistance (85/85 biased): 50V.
5		PCB simulation.
6	1039	Steady-state operation life: Condition B, T _J = +150°C minimum, 1,000 hrs, 32V, 10 mA, T _A = +45°C.
7	1039	HTRB: Condition A, +150°C, 1,000 hours, 48V.
	Electrical measurements	Group A, subgroup 2.
	Delta shift	See table III.

4.4.3.2 Group C sample selection. Samples for subgroups in group C shall be in accordance with MIL-PRF-19500.

4.4.4 Group E inspection. Group E inspection shall be performed for qualification or re-qualification only. The tests specified in table II herein must be performed to maintain qualification. Subgroup 7 and 8 are for characterization of the devices and have no pass or fail criteria. These steps are intended for user information only. Separate samples may be used for each subgroup, however, preconditioning shall be performed on all samples.

4.5 Method of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Input capacitance. This test shall be conducted in accordance with method 3240 of MIL-STD-750, except the output capacitor shall be omitted.

TABLE I. Group A inspection.

Inspection <u>1</u> /	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u> <u>2</u> /						
Resistance to solvents <u>3</u> /	1022	n = 15, c = 0				
<u>Subgroup 2</u>						
Collector to emitter breakdown voltage	3011	Bias condition D; I _C = 10 mA dc pulsed (see 4.5.1)	V _{(BR)CEO}	60		V dc
Collector to base cutoff current	3036	Bias condition D; V _{CB} = 60 V dc	I _{CBO1}		10	μA dc
Emitter to base cutoff current	3061	Bias condition D; V _{EB} = 6 V dc	I _{EB01}		10	μA dc
Collector to base cutoff current	3036	Bias condition D; V _{CB} = 45 V dc	I _{CBO2}		5	nA dc
Collector to emitter cutoff current	3041	Bias condition D; V _{CE} = 5 V dc	I _{CEO}		2	nA dc
Emitter to base cutoff current	3061	Bias condition D; V _{EB} = 5 V dc	I _{EB02}		2	nA dc
Collector to emitter cutoff current	3041	Bias condition C; V _{CE} = 45 V dc	I _{CES}		5	nA dc
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 1 μA dc	h _{FE1}	45		
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 10 μA dc	h _{FE2}	200	500	
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 100 μA dc	h _{FE3}	225	675	
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 500 μA dc	h _{FE4}	250	800	
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 1 mA dc	h _{FE5}	250	800	
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 10 mA dc pulsed (see 4.5.1)	h _{FE6}	225	800	
Collector to emitter voltage (saturated)	3071	I _C = 1.0 mA dc; I _B = 100 μA dc	V _{CE(sat)}		0.3	V dc
Base emitter voltage (nonsaturated)	3066	Test condition B; V _{CE} = 5 V dc; I _C = 100 μA dc	V _{BE(ON)}	0.5	0.7	V dc
<u>Subgroup 3</u>						
High-temperature operation		T _A = +150°C				
Collector to base cutoff current	3036	Bias condition D; V _{CB} = 45 V dc	I _{CBO3}		10	μA dc
Low-temperature operation		T _A = -55°C				
Forward-current transfer ratio	3076	V _{CE} = 5 V dc; I _C = 10 μA dc	h _{FE7}	35		

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4</u>						
Magnitude of common emitter small-signal short-circuit forward-current transfer ratio	3306	$V_{CE} = 5 \text{ V dc}; I_C = 50 \text{ } \mu\text{A dc}; f = 5 \text{ MHz}$	$ h_{fe} 1$	3.0		
Magnitude of common emitter small-signal short-circuit forward-current transfer ratio	3306	$V_{CE} = 5 \text{ V dc}; I_C = 500 \text{ } \mu\text{A dc}; f = 30 \text{ MHz}$	$ h_{fe} 2$	2.0	7.0	
Small-signal open-circuit output admittance	3216	$V_{CE} = 5 \text{ V dc}; I_C = 1.0 \text{ mA dc}; f = 1 \text{ kHz}$	h_{oe}		40	μmhos
Small-signal open-circuit reverse-voltage transfer ratio	3211	$V_{CE} = 5 \text{ V dc}; I_C = 1.0 \text{ mA dc}; f = 1 \text{ kHz}$	h_{re}		8.0×10^{-4}	
Small-signal short-circuit input impedance	3201	$V_{CE} = 5 \text{ V dc}; I_C = 1 \text{ mA dc}; f = 1 \text{ kHz}$	h_{ie}	3.5	24	$k\Omega$
Small-signal short-circuit forward current transfer ratio	3206	$V_{CE} = 5 \text{ V dc}; I_C = 1 \text{ mA dc}; f = 1 \text{ kHz}$	h_{fe}	250	900	
Open circuit output capacitance	3236	$V_{CB} = 5 \text{ V dc}; I_E = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{obo}		5.0	pF
Input capacitance (output open-circuited)	3240	$V_{EB} = 0.5 \text{ V dc}; I_C = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{ibo}		6.0	pF
Noise figure	3246	$f = 100 \text{ Hz}; V_{CE} = 5 \text{ V dc}; I_C = 10 \text{ } \mu\text{A dc}; R_g = 10 \text{ k}\Omega;$	NF1		7.5	dB
Noise figure	3246	$f = 1 \text{ kHz}; V_{CE} = 5 \text{ V dc}; I_C = 10 \text{ } \mu\text{A dc}; R_g = 10 \text{ k}\Omega;$	NF2		3	dB
Noise figure	3246	$f = 10 \text{ kHz}; V_{CE} = 5 \text{ V dc}; I_C = 10 \text{ } \mu\text{A dc}; R_g = 10 \text{ k}\Omega;$	NF3		2	dB
Noise figure (wideband)	3246	Noise bandwidth = 10 Hz to 15.7 kHz; $V_{CE} = 5 \text{ V dc}; I_C = 10 \text{ } \mu\text{A dc}; R_g = 10 \text{ k}\Omega;$	NF4		3	dB
<u>Subgroups 5, 6 and 7</u>						
Not applicable						

1/ For sampling plan see MIL-PRF-19500.

2/ For resubmission of failed subgroup A1, double the sample size of the failed test or sequence of tests. A failure in group A, subgroup 1 shall not require retest of the entire subgroup. Only the failed test shall be rerun upon submission.

3/ Not required for laser marked parts.

MIL-PRF-19500/674

TABLE II. Group E inspection (all quality levels) - for qualification only.

Inspection	MIL-STD-750 (unless otherwise noted)		Qualification
	Method	Conditions	
<u>Preconditioning</u>	JESD22-A113 <u>1/</u>	Level 1	All
<u>Subgroup 1</u>			
Temperature cycling (air to air)	1051	Test condition G, 1,000 cycles	n = 77, c = 0
Electrical measurements		See group A, subgroup 2.	
<u>Subgroup 2 2/</u>			n = 77, c = 0
Steady-state operation life	1039	1,000 hours, condition B.	
Electrical measurements		See group A, subgroup 2.	
<u>Subgroup 2a 2/</u>			n = 77, c = 0
HTRB	1039	1,000 hours, condition A.	
Electrical measurements		See group A, subgroup 2.	
<u>Subgroup 2b 2/</u>			n = 77, c = 0
Intermittent life	1037	Intermittent operation life: $V_{CB} = 10$ V dc , 15,000 cycles, $\Delta T_J \geq +100^\circ\text{C}$; forced air cooling allowed on cooling cycle only.	
Electrical measurements		See group A, subgroup 2.	
<u>Subgroup 3</u>			
Not applicable			
<u>Subgroup 4</u>			n = 77, c = 0
Moisture resistance	JESD22-A101 <u>1/</u>	1,000 hours	
Electrical measurements		See group A, subgroup 2.	
<u>Subgroup 4a</u>			n = 77, c = 0
Autoclave	JESD22-A102 <u>1/</u>	96 hours	
Electrical measurements		See group A, subgroup 2.	
<u>Subgroup 5</u>			
Thermal resistance	3131	See figures 3 and 4.	n = 10, c = 0

See footnotes at end of table.

TABLE II. Group E inspection (all quality levels) - for qualification only - Continued.

Inspection	MIL-STD-750 (unless otherwise noted)		Qualification
	Method	Conditions	
<u>Subgroup 6</u> ESD	JESD22-A112 MM & HBM <u>1/</u>		n = 30, c = 0 2 lots
<u>Subgroup 7</u> Moisture reflow sensitivity classification for surface mount devices	J-STD-20A <u>1/</u>		
<u>Subgroup 8</u> Parametric characterization		Group A, subgroup 2; -50°C, 25°C, +100°C	n = 25 for 3 lots

1/ Non-government standard document, see 2.3.

2/ Subgroups 2, 2a, and 2b do not need to be performed sequentially.

TABLE III. Groups B and C delta measurements.

Step	Inspection	MIL-STD-750		Symbol	Limit
		Method	Conditions		
1	Collector-base cutoff current	3036	Bias condition D, $V_{CB} = 45$ V dc	ΔI_{CB02} <u>1/</u>	Pre-test distribution to average $+3\sigma$ and -3σ . Post-test distribution to average $+4\sigma$ and -4σ of the pre-test results.
2	Forward current transfer ratio	3076	$V_{CE} = 5$ V dc; $I_C = 500$ uA dc; pulsed see 4.5.1	Δh_{FE4} <u>1/</u>	Pre-test distribution to average $+3\sigma$ and -3σ . Post-test distribution to average $+4\sigma$ and -4σ of the pre-test results (not to exceed 25 percent change from initial reading)

1/ Devices which exceed the group A limits for this test shall not be accepted.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department or Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation, and if required, the specific issue of individual documents referenced (see 2.2).
- c. Packaging requirements (see 5.1).
- d. Lead finish (see 3.4.1).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers' List (QML) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43216-5000.

Custodians:
Army - CR
Navy - NW
Air Force - 11
NASA - NA
DLA - CC

Preparing activity:
DLA - CC
(Project 5961-2465)

Review activity:
Army - MI

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
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I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-PRF-19500/674	2. DOCUMENT DATE 16 July 2001
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3. DOCUMENT TITLE
SEMICONDUCTOR DEVICE, TRANSISTOR, PLASTIC, NPN, SILICON, SWITCHING, LOW NOISE TYPE 2N2484UE1 JAN, JANTX, JANJ

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) COMMERCIAL DSN FAX EMAIL	7. DATE SUBMITTED

8. PREPARING ACTIVITY

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c. ADDRESS Defense Supply Center Columbus, ATTN: DSCC-VAC, P. O. Box 3990, Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533, Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888	